



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

**H1815**

### AUDIO FREQUENCY AMPLIFIER

### HIGH FREQUENCY OSC

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature..... -55~150

$T_j$ —Junction Temperature..... 150

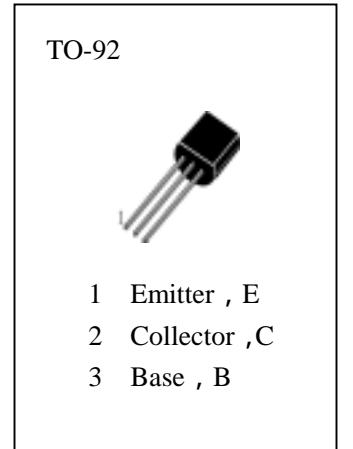
$P_C$ —Collector Dissipation..... 400mW

$V_{CBO}$ —Collector-Base Voltage..... 60V

$V_{CEO}$ —Collector-Emitter Voltage..... 50V

$V_{EBO}$ —Emitter-Base Voltage..... 5V

$I_C$ —Collector Current..... 150mA



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{CBO}$	Collector Cut-off Current			100	nA	$V_{CB}=60V, I_E=0$
$I_{EBO}$	Emitter Cut-off Current			100	nA	$V_{EB}=5V, I_C=0$
$HFE(1)$	DC Current Gain	70		700		$V_{CE}=6V, I_C=2mA$
$HFE(2)$		25				$V_{CE}=6V, I_C=150mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			250	mV	$I_C=100mA, I_B=10mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.0	V	$I_C=100mA, I_B=10mA$
$BV_{CBO}$	Collector-Base Breakdown Voltage	60			V	$I_C=100 \mu A, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	50			V	$I_C=1mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	5			V	$I_E=100 \mu A, I_C=0$
$f_T$	Current Gain-Bandwidth Product	80			MHz	$V_{CE}=10V, I_C=1mA$

### hfe Classification

O	Y	GR	BL
70—140	120—240	200—400	350—700